

Silicon NPN Power Transistors

2SC2768

DESCRIPTION

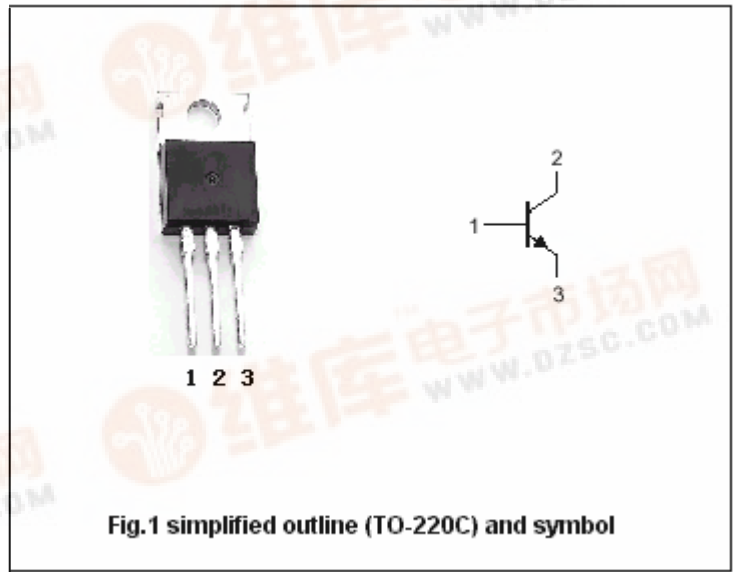
- With TO-220C package
- High speed switching
- High reliability

APPLICATIONS

- Switching regulators
- Ultrasonic generators
- High frequency inverters
- General purpose power amplifiers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	250	V
V _{CEO}	Collector-emitter voltage	Open base	200	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		6	A
I _B	Base current		1.5	A
P _C	Collector power dissipation	T _C =25	40	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction case	3.0	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	200			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =100 μ A ; I _E =0	250			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =100 μ A ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A; I _B =0.8A			0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2A; I _B =0.8A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =250V ; I _E =0			100	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			100	μ A
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	20			

Switching times

t _{on}	Turn-on time	I _C =4A; I _{B1} =-I _{B2} =-0.4A R _L =20			1.0	μ s
t _{stg}	Storage time				2.0	μ s
t _f	Fall time				1.0	μ s

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PACKAGE OUTLINE

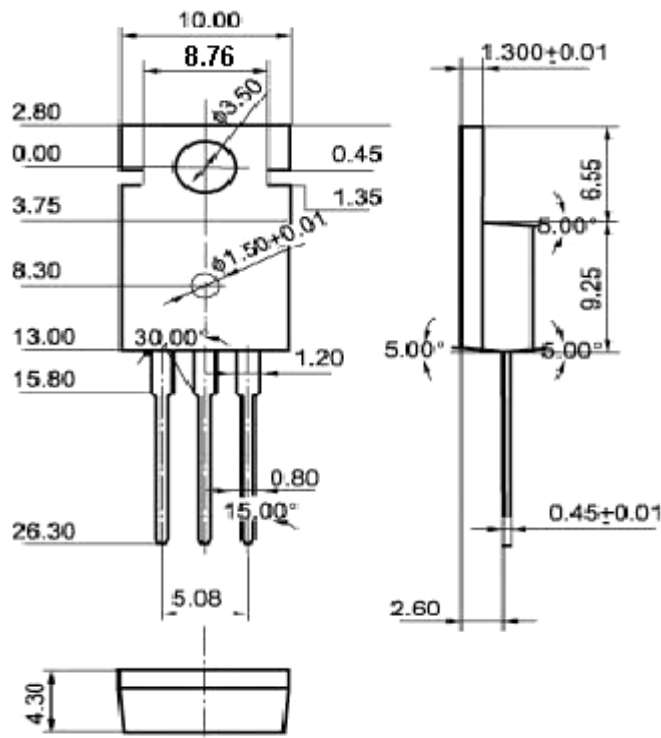


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)

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